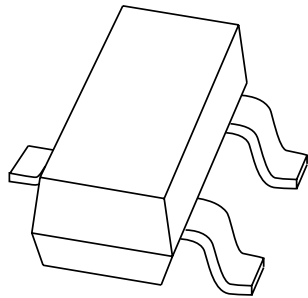


DATA SHEET



BAT54W series Schottky barrier (double) diodes

Product specification
Supersedes data of October 1993

1996 Mar 19

Schottky barrier (double) diodes

BAT54W series

FEATURES

- Low forward voltage
- Guard ring protected
- Very small SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes.

DESCRIPTION

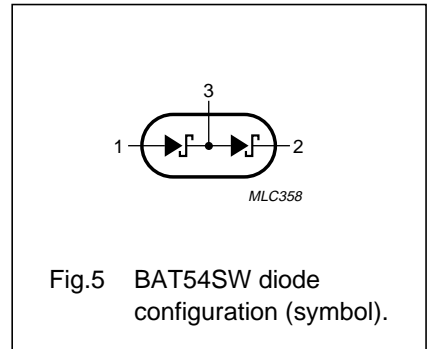
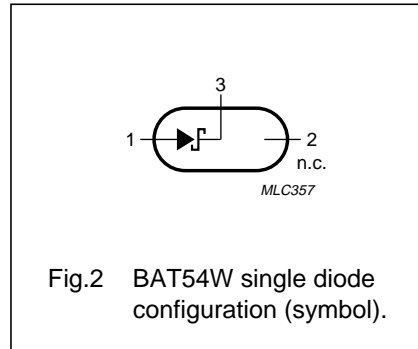
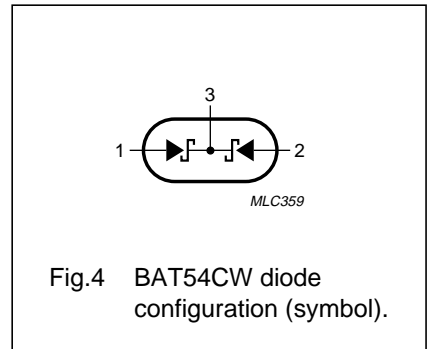
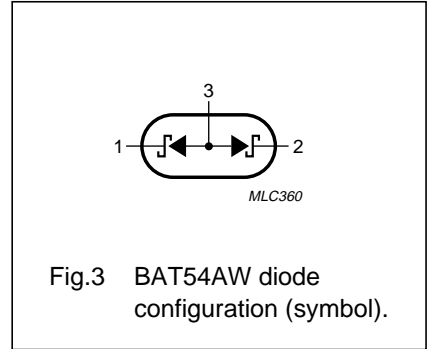
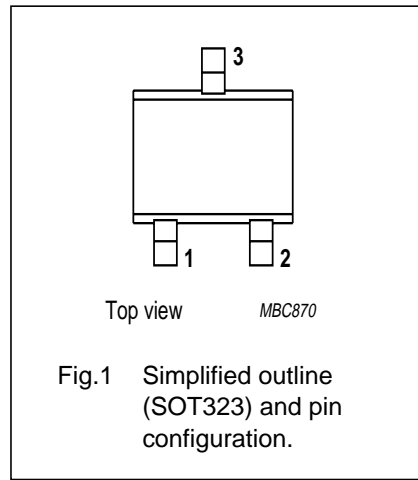
Planar Schottky barrier diodes encapsulated in a SOT323 very small plastic SMD package. Single diodes and double diodes with different pinning are available.

MARKING

TYPE NUMBER	MARKING CODE
BAT54W	L4
BAT54AW	42
BAT54CW	43
BAT54SW	44

PINNING

PIN	BAT54			
	W	AW	CW	SW
1	a	k ₁	a ₁	a ₁
2	n.c.	k ₂	a ₂	k ₂
3	k	a ₁ , a ₂	k ₁ , k ₂	k ₁ , a ₂



Schottky barrier (double) diodes

BAT54W series

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_R	continuous reverse voltage		–	30	V
I_F	continuous forward current		–	200	mA
I_{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ s}; \delta \leq 0.5$	–	300	mA
I_{FSM}	non-repetitive peak forward current	$t_p < 10 \text{ ms}$	–	600	mA
P_{tot}	total power dissipation (per package)	$T_{amb} \leq 25 \text{ }^\circ\text{C}$	–	200	mW
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	125	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+125	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS $T_{amb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V_F	forward voltage	see Fig.6 $I_F = 0.1 \text{ mA}$ $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 30 \text{ mA}$ $I_F = 100 \text{ mA}$	240 320 400 500 800	mV mV mV mV mV
I_R	reverse current	$V_R = 25 \text{ V}$; note 1; see Fig.7	2	μA
t_{rr}	reverse recovery time	when switched from $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA}$; $R_L = 100 \text{ } \Omega$; measured at $I_R = 1 \text{ mA}$; see Fig.9	5	ns
C_d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 1 \text{ V}$; see Fig.8	10	pF

Note1. Pulsed test: $t_p = 300 \text{ } \mu\text{s}$; $\delta = 0.02$.**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th \text{ j-a}}$	thermal resistance from junction to ambient	note 1	625	K/W

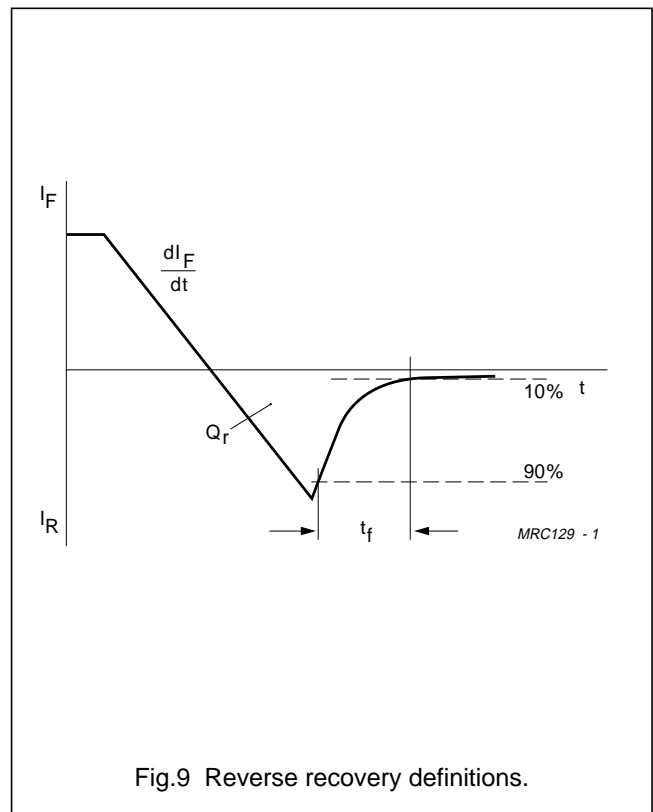
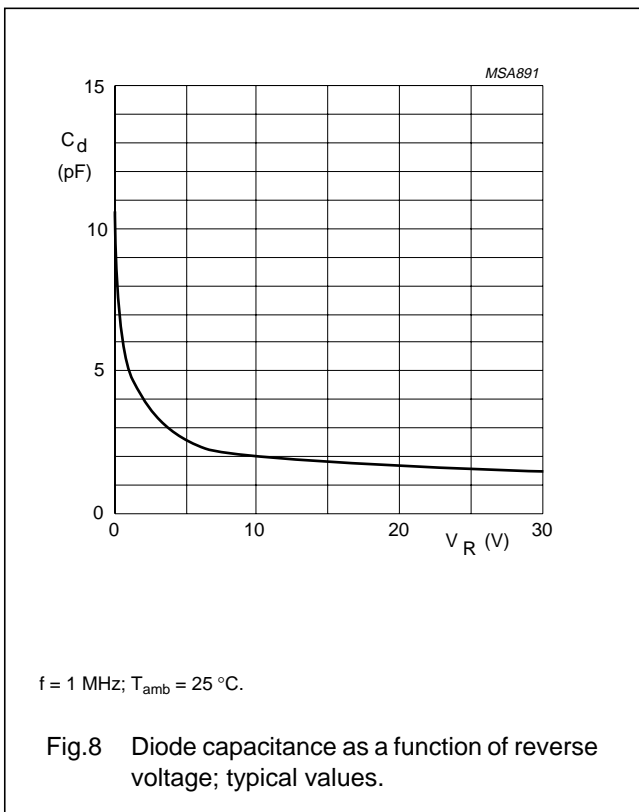
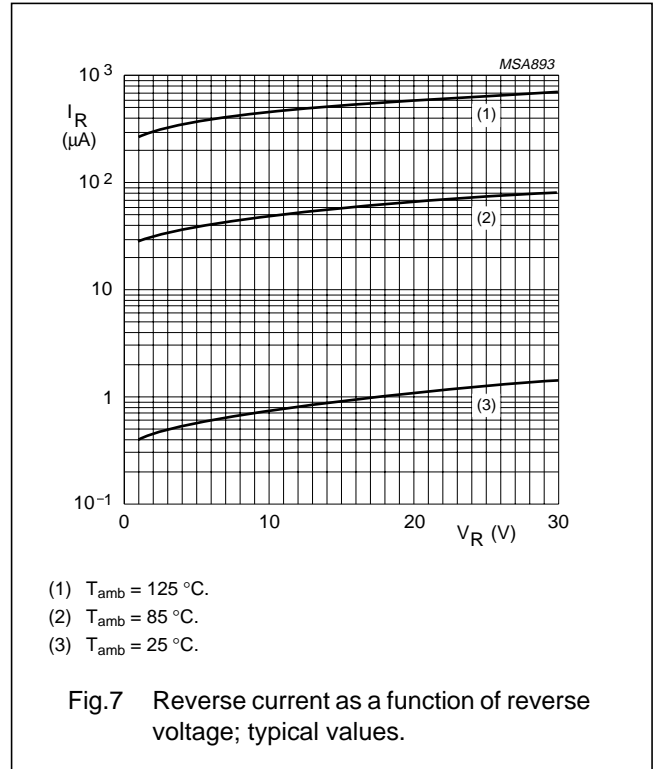
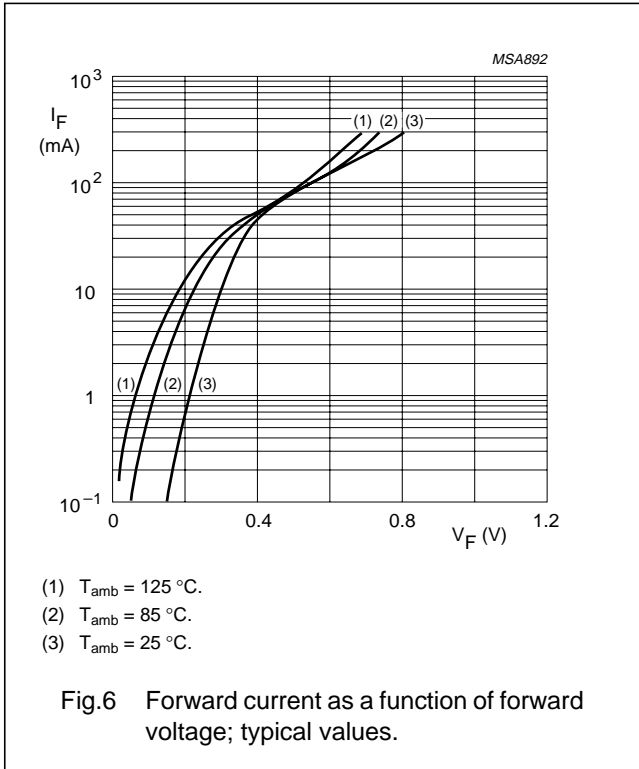
Note

1. Refer to SOT323 standard mounting conditions.

Schottky barrier (double) diodes

BAT54W series

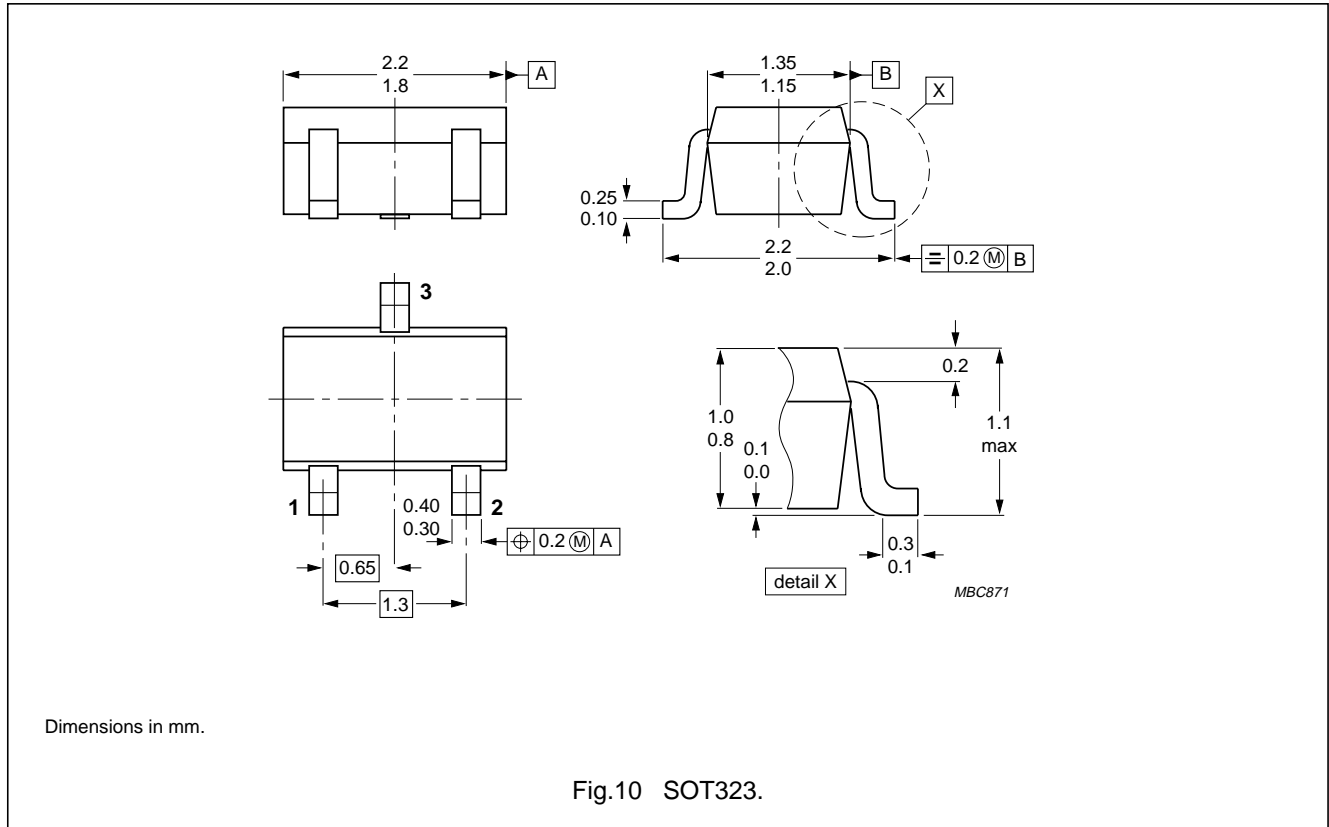
GRAPHICAL DATA



Schottky barrier (double) diodes

BAT54W series

PACKAGE OUTLINE



DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.